

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	9	("4103342" or "4686552" or "4927779" or "5134616" or "5567962" or "5606189" or "5780335" or "6101117" or "6246083") pn.	USPAT; US-PGPUB	2003/02/26 11:11
2	BRS	0	kowalshi.in.	USPAT; US-PGPUB	2003/02/26 11:12
3	BRS	532	kowalski.in.	USPAT; US-PGPUB	2003/02/26 11:12
4	BRS	33	kowalski.in. and capacitor	USPAT; US-PGPUB	2003/02/26 12:16
5	IS&R	10	(("4785337") or ("4833094") or ("5384789") or ("4830978") or ("4910567") or ("4916524") or ("5198383") or ("5364808") or ("5468980") or ("5973952")).PN.	USPAT; US-PGPUB	2003/02/26 12:17
6	IS&R	40	(("5999440") or ("6207493") or ("4791610") or ("5798545") or ("5317540") or ("5432733") or ("6136652") or ("4864375") or ("4980734") or ("5640350") or ("4388121") or ("4574465") or ("4883543") or ("5208657") or ("5300450") or ("5334548") or ("5383150") or ("5559734") or ("5753420") or ("5999439") or ("4763181") or ("5442211") or ("5618745") or ("6194311") or ("5465249") or ("5872373") or ("6151244") or ("4761385") or ("4786954") or ("4864374") or ("4999811") or ("5365477") or ("5508542") or ("5635419") or ("5671182") or ("5736761") or ("5770510") or ("5866928") or ("5959322") or ("6066870")).PN.	USPAT; US-PGPUB	2003/02/26 12:27
7	BRS	15	hisamoto.in. and delta	USPAT; US-PGPUB	2003/02/26 12:27
8	BRS	9	4103342.URPN.	USPAT	2003/02/26 13:45
9	BRS	3	("4103342" "4715015" "4792922").PN.	USPAT	2003/02/26 13:49
10	BRS	2	5329479.URPN.	USPAT	2003/02/26 13:50
11	BRS	3	("3463992" "3585185" "3938109").PN.	USPAT	2003/02/26 13:52
12	BRS	3	("3463992" "3585185" "3938109").PN.	USPAT	2003/02/26 13:53
13	BRS	9	4103342.URPN.	USPAT	2003/02/26 13:53
14	BRS	2	jp-61240497-\$.did. or jp-62065295-\$.did.	EPO: JPO; DERWENT	2003/02/26 14:09

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 5329479 A	12	Dynamic semiconductor memories	365/149	365/206	Ota, Yoshiji et al.
2	US 4888733 A	6	Non-volatile memory cell and sensing method	365/145	365/149; 365/189.07	Mobley, Kenneth J.
3	US 6198151 B1	22	Semiconductor device, semiconductor integrated circuit device, and method of manufacturing same	257/520	257/301; 257/E27.084	Wada, Toshio
4	US 5943279 A	8	Semiconductor memory integrated circuit	365/205	365/149; 365/207; 365/208	Wada, Toshio

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 5567962 A	55	Semiconductor memory device	257/296	257/306; 257/530; 257/E27.078; 257/E27.085; 257/E27.103; 257/E29.13	Miyawaki, Mamoru et al.
2	US 4103342 A	6	Two-device memory cell with single floating capacitor	365/149	365/208	Miersch, Ekkehard Fritz et al.

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/064,869 on February 20, 2003

Combined Classifications

16 365/149
9 257/296
9 257/304
8 257/302
6 257/301
6 257/E27.092
5 257/305
5 257/E27.085
4 257/300
4 257/E27.084
4 257/E27.086
4 365/174
4 365/51
4 438/243
4 438/386
3 257/68
3 257/E27.093
3 257/E29.346
3 365/226
3 438/242
3 438/246
2 257/303
2 257/347
2 257/382
2 257/390
2 257/905
2 257/906
2 257/907
2 257/E27.075
2 257/E27.091
2 257/E27.112
2 365/145
2 365/177
2 365/180
2 365/189.01
2 365/189.05
2 365/63
2 365/69
2 365/72
2 438/248
2 438/249
2 438/250
2 438/253
2 438/262
2 438/449
2 438/554

- 16 365/149 (6 OR, 10 XR)
Class 365 : STATIC INFORMATION STORAGE AND RETRIEVAL
365/129 SYSTEMS USING PARTICULAR ELEMENT
365/149 .Capacitors
- 9 257/296 (4 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET,
MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
gate transistor combined with capacitor (e.g., dynamic
memory cell)
- 9 257/304 (2 OR, 7 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET,
MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
gate transistor combined with capacitor (e.g., dynamic
memory cell)
257/301 ...Capacitor in trench
257/304Storage node isolated by dielectric from
semiconductor substrate
- 8 257/302 (3 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET,
MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
gate transistor combined with capacitor (e.g., dynamic
memory cell)
257/301 ...Capacitor in trench
257/302Vertical transistor
- 6 257/301 (5 OR, 1 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET,
MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
gate transistor combined with capacitor (e.g., dynamic
memory cell)
257/301 ...Capacitor in trench
- 6 257/E27.092 (0 OR, 6 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E27.001 DEVICE CONSISTING OF A PLURALITY OF
SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR
ON A COMMON SUBSTRATE, E.G., INTEGRATED CIRCUIT DEVICE
(EPO)
257/E27 009 .Including semiconductor component with at
least one potential barrier or surface barrier adapted for
rectifying, oscillating, amplifying, or switching, or

including integrated passive circuit elements (EPO)
257/E27.01 ..With semiconductor substrate only (EPO)
257/E27.07 ...Including a plurality of individual
 components in a repetitive configuration (EPO)
257/E27.081 Including field-effect component (EPO)
257/E27.084 Dynamic random access memory. DRAM.
 structure (EPO)
257/E27.085 One-transistor memory cell structure.
 i.e., each memory cell containing only one transistor (EPO)

257/E27.092 Capacitor in trench (EPO)

5 257/305 (0 OR. 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 (E) FIELD EFFECT Device
257/288 ..(E) Having insulated electrode (e.g., MOSFET,
 MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
 gate transistor combined with capacitor (e.g., dynamic
 memory cell)
257/301 ...Capacitor in trench
257/305 With means to insulate adjacent storage
 nodes (e.g., channel stops or field oxide)

5 257/E27.085 (0 OR. 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/E27.001 DEVICE CONSISTING OF A PLURALITY OF
 SEMICONDUCTOR OR OTHER SOLID STATE COMPONENTS FORMED IN OR
 ON A COMMON SUBSTRATE. E.G., INTEGRATED CIRCUIT DEVICE
 (EPO)
257/E27.009 ..Including semiconductor component with at
 least one potential barrier or surface barrier adapted for
 rectifying, oscillating, amplifying, or switching, or
 including integrated passive circuit elements (EPO)
257/E27.01 ..With semiconductor substrate only (EPO)
257/E27.07 ...Including a plurality of individual
 components in a repetitive configuration (EPO)
257/E27.081 Including field-effect component (EPO)
257/E27.084 Dynamic random access memory. DRAM.
 structure (EPO)
257/E27.085 One-transistor memory cell structure.
 i.e., each memory cell containing only one transistor (EPO)

4 257/300 (1 OR. 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/213 (E) FIELD EFFECT Device
257/288 ..(E) Having insulated electrode (e.g., MOSFET,
 MOS diode)
257/296 ..(E) Insulated gate capacitor or insulated
 gate transistor combined with capacitor (e.g., dynamic
 memory cell)
257/300 ...Capacitor coupled to, or forms gate of,
 insulated gate field effect transistor (e.g.,
 nondestructive readout dynamic memory cell structure)

PLUS Search Results for S/N 10/064.869. Searched February 20, 2003 (Top 50)

4785337	5999440	4388121	4763181	4999811
4833094	6207493	4574465	5442211	5365477
5384789	4791610	4883543	5618745	5508542
4830978	5798545	5208657	6194311	5635419
4910567	5317540	5300450	5465249	5671182
4916524	5432733	5334548	5872373	5736761
5198383	6136652	5383150	6151244	5770510
5364808	4864375	5559734	4761385	5866928
5468980	4980734	5753420	4786954	5959322
5973952	5640350	5999439	4864374	6066870